

ABSTRACT

A boron phosphide-based semiconductor light-emitting device includes a substrate of silicon single crystal, a
5 first cubic boron phosphide-based semiconductor layer that is provided on a surface of the substrate and contains twins, a light-emitting layer that is composed of a hexagonal Group III nitride semiconductor and provided on the first cubic boron phosphide-based semiconductor layer and a second cubic
10 boron phosphide-based semiconductor layer that is provided on the light-emitting layer, contains twins and has a conduction type different from that of the first cubic boron phosphide-based semiconductor layer.